˜Yت / Descriptions

TO-220FL N MOS

N-CHANNEL MOSFET in a TO-220FL Plastic Package.

● Ȅ / Features

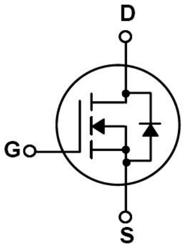
Low gate charge, low crss, fast switching,Have good Electromagnetic Interference performance.

۷ ږ / Applications

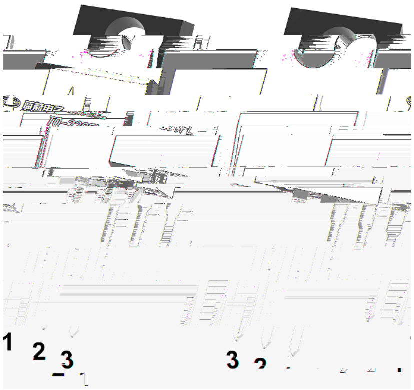
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

ɲ ق ặ ء ع / Equivalent Circuit



ẫ ⅄ ŭ / Pinning



PIN1 G PIN 2 D PIN 3 S

ŧ ʜ ב / Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	7.0	A
Drain Current	I_D(Tc=100)	4.4	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	425	mJ
Avalanche Current	I_{AR}	9.9	A
Power Dissipation	P_D(Tc=25)	35	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	
Junction to Ambient	$R_{\theta JA}$	62.5	/W
Junction to Case	$R_{\theta JC}$	3.6	/W

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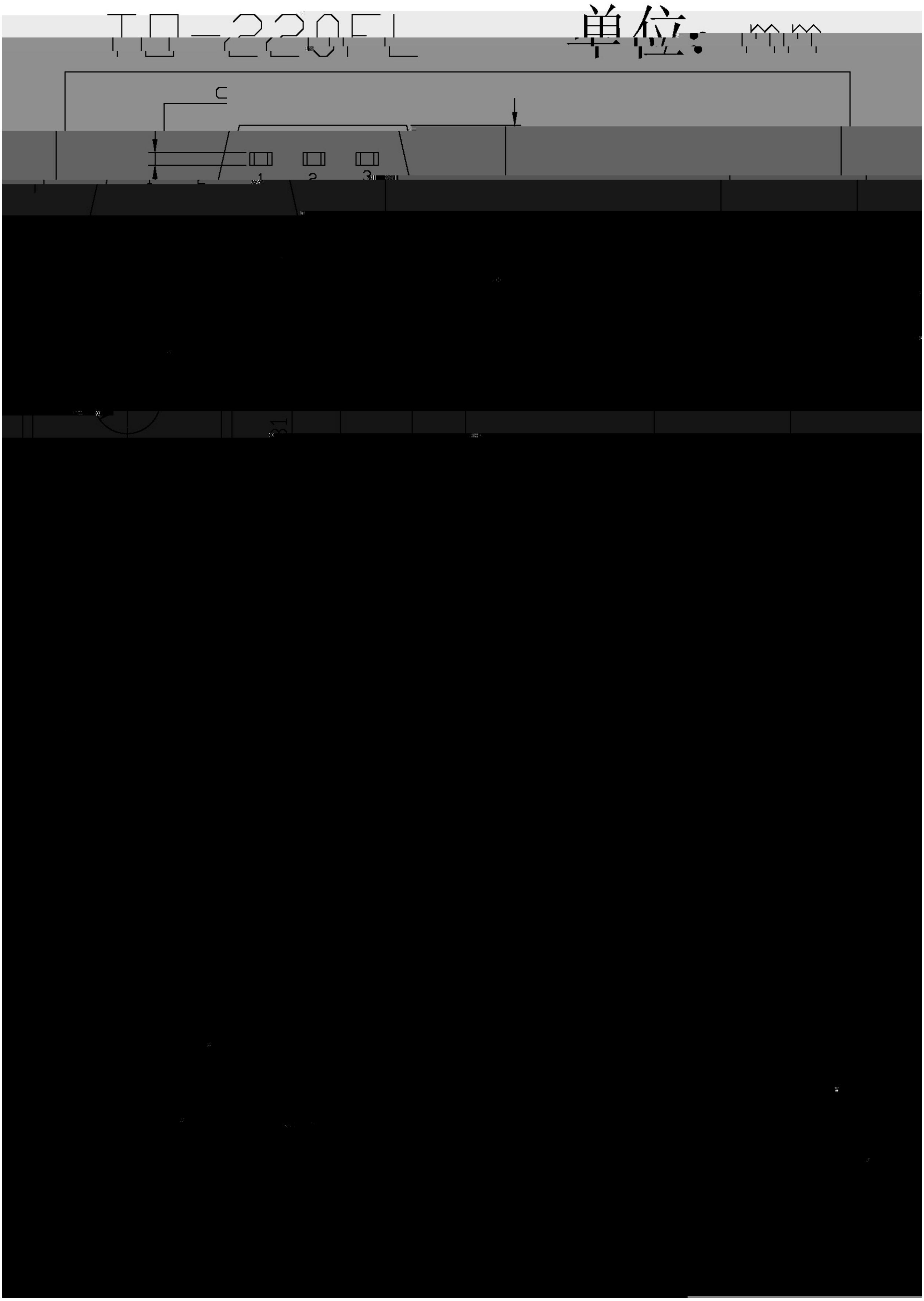
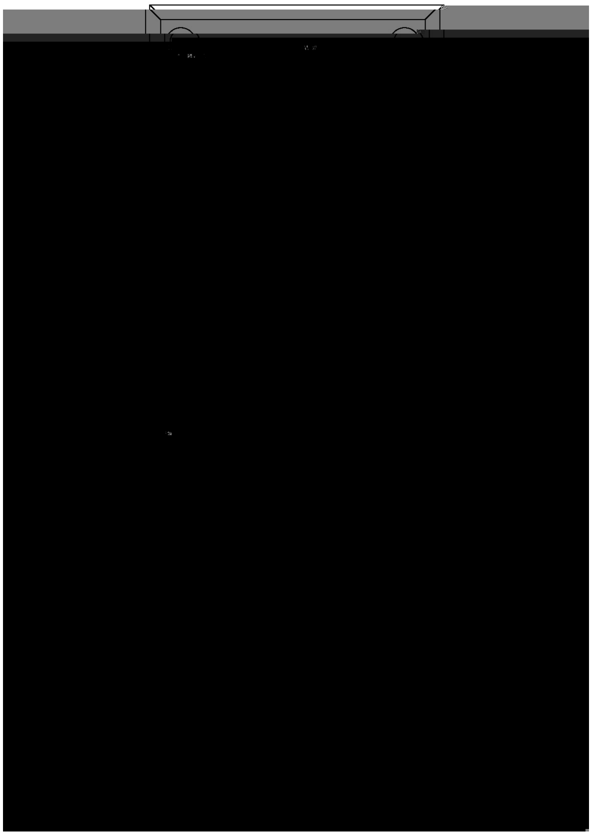
Parameter Symbol

ᵁ ẺÒḺ ʃ / Package Dimensions





↓ ş ╖ ẘΈ Ⅵ ƒ (ὢ ٽ) / Temperature Profile for Dip Soldering(Pb-Free)

1 25 150 60 90sec;
2 255±5 5±0.5sec;
3 2 10 /sec.

Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

⅃ ü q ꞈ ˋY Ţ / Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

ʖ ㄴ ⪡— / Packaging SPEC.

/ TUBE

Package Type	Units	Dimension	(unit mm^3